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Photocurrent Measurements of Carbon Nanotube PN Junctions

NATHANIEL GABOR, ZHAOHUI ZHONG, Laboratory of Atomic and Solid State Physics, Cornell University, KEN BOSNICK, National Institute for Nanotechnology, National Research Council of Canada, JIWOONG PARK, Chemistry and Chemical Biology, Cornell University, PAUL MCEUEN, Laboratory of Atomic and Solid State Physics, Cornell University — Gated p-n junctions in semiconducting nanotubes have recently drawn much attention for their electronic and optoelectronic characteristics [1,2,3]. We investigate the photocurrent response at a nanotube gated p-n junction using a focused laser illumination source. We find that the photocurrent at zero source-drain bias increases linearly with optical power for the component of light along the length of the nanotube. Scanned photocurrent imaging demonstrates that carrier generation occurs primarily between the p- and n- type segments of the device. Measurements in an optical cryostat down to 4K reveal large photoresponse and step-like structure in the reverse bias photocurrent. These results show that nanotube p-n junctions are highly sensitive, nanoscale photodetectors. [1] J.U. Lee et al, App. Phys. Lett. **85**, 145 (2004). [2] J.U. Lee, App. Phys. Lett. **87**, 073101 (2005). [3] K. Bosnick et al, App. Phys. Lett. **89**, 163121 (2006).

Nathaniel Gabor
Laboratory of Atomic and Solid State Physics, Cornell University

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